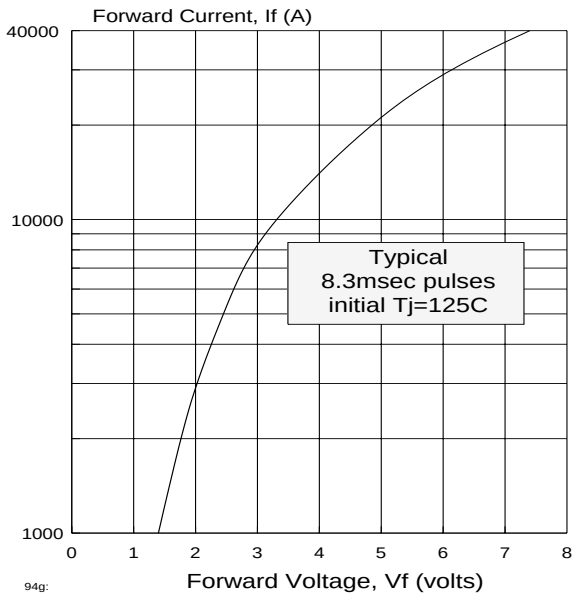
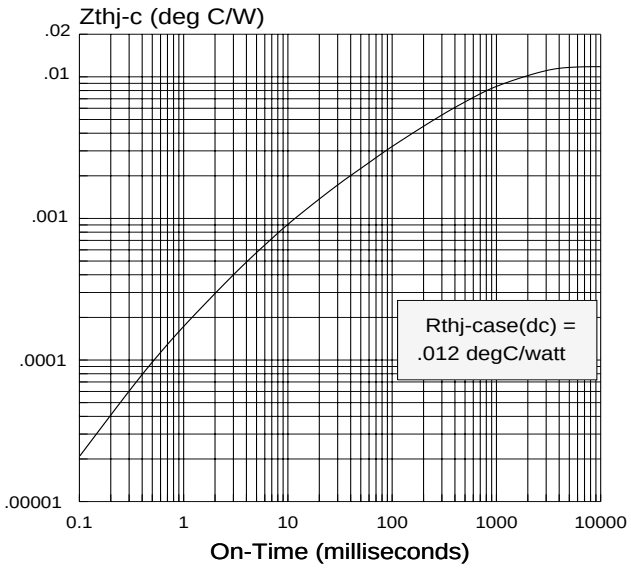
SDD216
77mm Fast Recovery DIODE
2500V / 2900Arms

The SDD216 fast recovery diode is designed for use in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer a new advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 77mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.

FORWARD CONDUCTION CHARACTERISTIC



THERMAL IMPEDANCE vs. ON-TIME



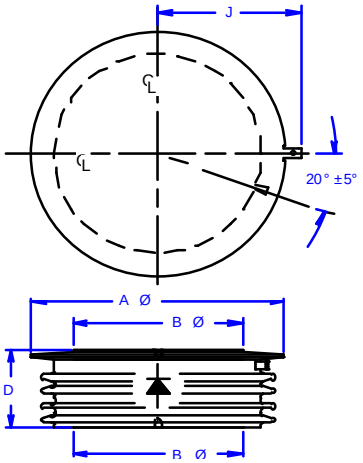
MAXIMUM RATINGS & PARAMETERS

Maximum repetitive peak reverse voltage	**V_{RRM}**	**T_J = 0 to +125°C**	**to 2500**	**V**
Maximum forward average & RMS current ratings	**$I_{F(AV)}$**	**T_{case} 70°C**	**1850**	**A**
	I_{RMS}		**2900**	
Maximum reverse leakage current	**I_{RRM}**		**200**	**ma**
Forward voltage drop	**V_{FM}**	**I_T=2000A t_p=8.3ms T_J=125°C**	**1.75**	**V**
Maximum peak recovery current*	**I_{RR}**	**@ 10 A/us**	**40**	**A**
		@ 100 A/us	**300**	
Maximum recovery charge	**Q_{RR}**	**@ 10 A/us**	**128**	**uC**
		@100A/us	**720**	

SELECTION TABLE

MODEL	V_{RRM} Tj = 0 to 125°C
SDD216DK	2500 volts
SDD216TT	2000

MECHANICAL OUTLINE



AΦ = 4.35 in (110.5 mm)
BΦ= 2.88 in (73.2 mm)
D= 1.07 in (27.2 mm)

CLAMPING FORCE REQUIRED
7000 - 9000 lb / 31.1 - 40.0 kN

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